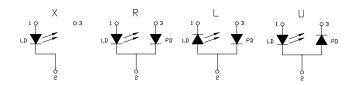
■-ø3,55±0.1→

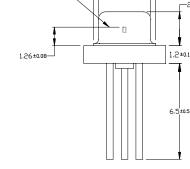
660nm 50mW 60°C Reliable High Power Operation

Applications

Light source for high power industrial & medical applications

•Pin connections

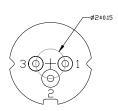




ø5.6⁰-0.025

Absolute maximum ratings

Parameter	Symbol	Condition	Rating	Unit
Light output power	P _o	CW	55	mW
Reverse voltage (LD)	V_{RL}	CW	2	V
Reverse voltage (PD)	V_{RD}	-	30	V
Forward current (PD)	I _{FD}	-	10	mA
Case temperature	T _C	CW	-10~+60	°C
Storage temperature	Ts	-	-40~+75	°C



•Electrical and optical characteristics (T_c=25 °C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Peak wavelength		650	660	665	nm	P _o =50mW
Threshold current	I _{th}	-	45	70	mA	
Operating current	l _{op}	-	100	120	mA	
Operating voltage	V_{op}	-	2.5	2.8	V	
Differential efficiency		0.7	1.0	1.3	mW/mA	P _o =35-45mW
Monitor current (For TR,TL type)	l _m	-	0.5	-	mA	P _o =50mW, V _{RD} =5V
Parallel divergence angle	//	-	9	-	deg	
Perpendicular divergence angle		-	20	-	deg	
Parallel FFP deviation angle	//	-	-	±2	deg	P _o =50mW
Perpendicular FFP deviation angle		-	-	±2	deg	
Emission point accuracy	хуг	-	-	±80	um	

Do not operate the device above the maximum rating condition, even momentarily. It may cause unexpected permanent damage to the device.
 Semiconductor laser device is very sensitive to electrostatic discharge. High voltage spike current may change the characteristics of the device, or malfunction at any time during its service period. Therefore, proper measures for preventing electrostatic discharge are strongly recommended.
 Effective heat sink can help the device operates under a more relax condition; as a result, a more stable characteristics and better reliability can be achieved. So it is

recommended that always apply proper heat sink before the device is operating.

4. Do not look into the laser beam directly by bare eyes. The laser beam may cause severe damage to human eyes.